

### Description

The BSS138K uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

#### **General Features**

 $V_{DS} = 50V I_D = 0.22A$ 

 $R_{DS(ON)} < 2.0\Omega @V_{GS}=10V$ 

### Application

Battery protection

Load switch

Uninterruptible power supply

### Package Marking and Ordering Information

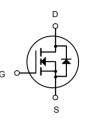
Product ID	Pack	Marking	Qty(PCS)
BSS138K	SOT-23	SS	3000

### Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

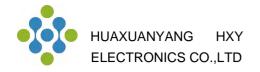
Symbol	Parameter	Limit	Unit		
VDS	Drain-Source Voltage	50	V		
Vgs	Gate-Source Voltage		±20	V	
	Continuous Drain Current (TJ =150°C)	T <sub>A</sub> =25℃	0.22		
Ι <sub>D</sub>		T <sub>A</sub> =100 ℃	0.13	A	
Ідм	Drain Current-Pulsed (Note 1)		0.88	А	
PD	Maximum Power Dissipation	0.35	W		
Тј,Тѕтс	Operating Junction and Storage Temperature Range		-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		357	°C <b>/W</b>	







N-Channel MOSFET



## Electrical Characteristics (T\_A=25 $^{\circ}\!\!^{\circ}\!$

Parameter	Symbol	Test Condition	Min	Тур	Мах	Units
Off characteristics						
Drain-source breakdown voltage	V(BR)DSS	Vgs = 0V, Id =250µA	50			V
Gate-body leakage	I <sub>GSS</sub>	VDS =0V, VGS =±20V			±100	nA
	I <sub>DSS</sub>	VDS =50V, VGS =0V			0.5	μA
Zero gate voltage drain current		VDS =30V, VGS =0V			100	nA
On characteristics						
Gate-threshold voltage (note 1)	VGS(th)	VDS =V <sub>GS</sub> , ID =1mA	0.8		1.5	V
	RDS(on)	Vgs =10V, ID =0.22A		1.1	2.0	Ω
Static drain-source on-resistance (note 1)		Vgs =4.5V, Id =0.22A		1.5	3	
Forward transconductance (note 1)	<b>g</b> fs	VDS =10V, ID =0.22A	0.12			S
Dynamic characteristics (note 2)					•	
Input capacitance	C <sub>iss</sub>			27		pF
Output capacitance	Coss	Vps =25V,Vgs =0V, f=1MHz		13		
Reverse transfer capacitance	C <sub>rss</sub>			6		
Switching characteristics			•			
Turn-on delay time (note 1,2)	td(on)				5	
Rise time (note 1,2)	tr	V <sub>DD</sub> =30V, V <sub>DS</sub> =10V,			18	ns
Turn-off delay time (note 1,2)	td(off)	ID =0.29A,R <sub>GEN</sub> =6Ω			36	
Fall time (note 1,2)	tr				14	
Drain-source body diode characteristics	;		·			
Body diode forward voltage (note 1)	$V_{\text{SD}}$	I <sub>S</sub> =0.44A, V <sub>GS</sub> = 0V			1.4	V

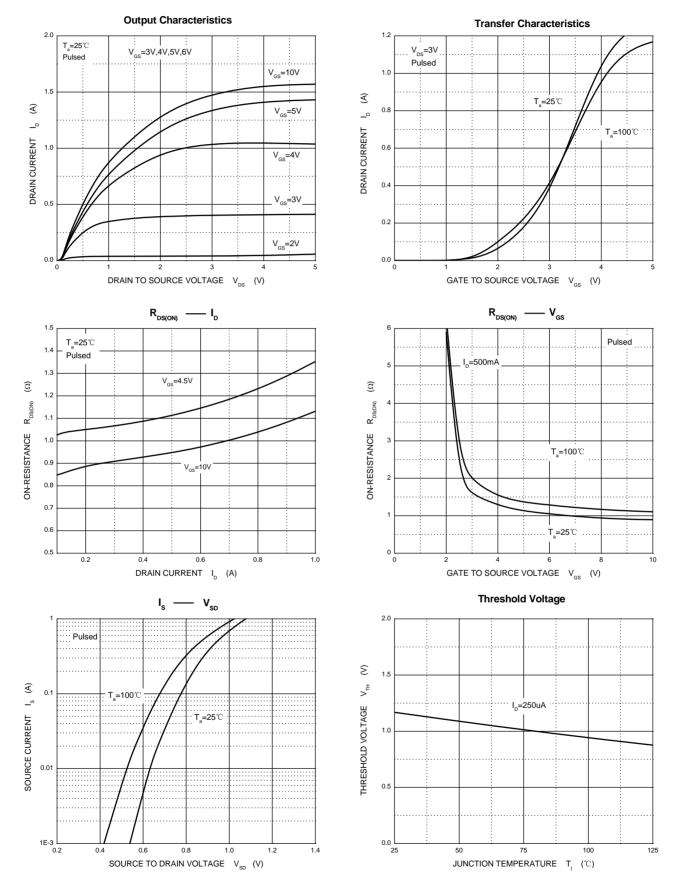
Notes:

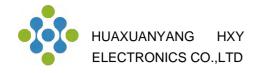
- 1. Pulse Test ; Pulse Width ≤300µs, Duty Cycle ≤2%.
- 2. These parameters have no way to verify.



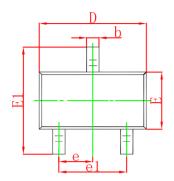
# N-Channel Enhancement Mode MOSFET

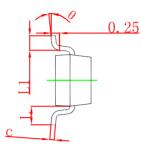
## **Typical Characteristics**

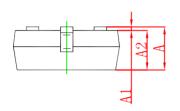




## **SOT-23 Package Outline Dimensions**

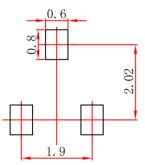






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## SOT-23 Suggested Pad Layout



Note:

1.Controlling dimension in millimeters.

2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.



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